



CE65H270TOBI

CoreGaN 650V GaN HEMT

Description

The CE65H270TOBI Series 650V, 270mΩ gallium nitride (GaN) FETs are normally-off devices.

Coreenergy GaN FETs offer better efficiency through lower gate charge, faster switching speeds, and lower dynamic onresistance, delivering significant advantages over traditional silicon (Si) devices.

Coreenergy is a leading-edge wide band gap supplier with world-class innovation .

Automotive

- Adapter
- Renewable energy
- Telecom and data-com
- Servo motors
- Industrial
- Automotive

General Features

Easy to drive—compatible with standard gate drivers

Low conduction and switching losses

RoHS compliant and Halogen-free

Benefits

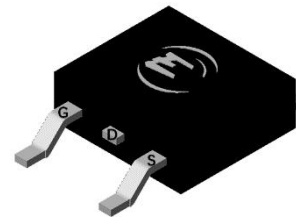
Increased efficiency through fast switching

Increased power density

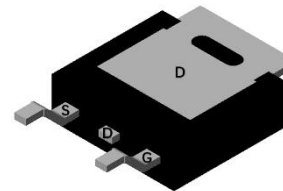
Reduced system size and weight

Ordering Information

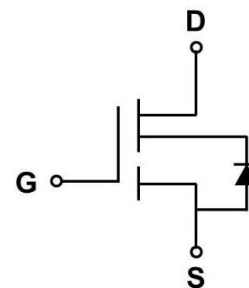
Part Number	Package	Package Configuration
CE65H270TOBI	TO252	Drain



Top



Bottom



Circuit Symbol

Features

BV_{DSS}	$R_{DS(on)}$	I_{DS}	Q_G
650V	270mΩ	7.9A	7.2nC



Absolute Maximum Ratings

$T_C=25^\circ\text{C}$ unless otherwise stated

Symbol	Parameter	Limit value	Unit	
V_{DSS}	Drain to source voltage ($T_J = -55^\circ\text{C}$ to 150°C)	650		
$V_{(TR)DSS}$	Drain to source voltage-transient ^a	900	V	
V_{GSS}	Gate to source voltage	-20~+20		
I_D	Continuous drain current @ $T_C=25^\circ\text{C}$ ^b	7.9	A	
	Continuous drain current @ $T_C=125^\circ\text{C}$ ^b	3.5		
I_{DM}	Pulse drain current (pulse width: 100 μs)	30	A	
P_D	Maximum power dissipation @ $T_C=25^\circ\text{C}$	32	W	
T_C	Operating temperature	Case	-55~150	$^\circ\text{C}$
T_J		Junction	-55~150	$^\circ\text{C}$
T_S	Storage temperature	-55~150	$^\circ\text{C}$	

a. In off-state, spike duty cycle $D<0.01$, spike duration $<1\mu\text{s}$

b. For increased stability at high current operation



Thermal Resistance

Symbol	Parameter	Limit value	Unit
$R_{\theta JC}$	Junction-to-case	3.9	$^{\circ}\text{C} / \text{W}$



Electrical Parameters

T_J=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
V _{(BL)DSS}	Drain-source voltage	650	-	-	V	V _{GS} = 0V
V _{GS(th)}	Gate threshold voltage	-	1.9	-	V	V _{DS} = 1V, I _{DS} = 1mA
ΔV _{GS(th)/T_J}	Gate threshold voltage temperature coefficient	-	-7	-	mV/°C	
R _{DS(on)}	Drain-source on-resistance	-	270	320	mΩ	V _{GS} = 10V, I _D = 1A, T _J = 25°C
		-	570	-		V _{GS} = 10V, I _D = 1A, T _J = 150°C
I _{DSS}	Drain-to-source leakage current	-	-	10	μA	V _{DS} = 650V, V _{GS} = 0V, T _J = 25°C
		-	-	100		V _{DS} = 650V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-source forward leakage current	-	-	±100	nA	V _{GS} = ±20V
C _{ISS}	Input capacitance	-	243	-	pF	V _{GS} = 0V, V _{DS} = 400V, f = 1MHz
C _{OSS}	Output capacitance	-	10	-		
C _{RSS}	Reverse capacitance	-	0.8	-		
Q _G	Total gate charge	-	7.2	-	nC	V _{DS} = 400V, V _{GS} = 0V to 10V, I _D = 1A
Q _{GS}	Gate-source charge	-	2.1	-		
Q _{GD}	Gate-drain charge	-	0.9	-		
Q _{OSS}	Output charge	-	17	-	nC	V _{GS} = 0V, V _{DS} = 0V to 400V, f = 1MHz
t _{D(on)}	Turn-on delay	-	6	-	ns	V _{DS} = 400V, V _{GS} = 0V to 10V, I _D = 2.1A, R _{G-on(ext)} = 6.8Ω, R _{G-off(ext)} = 2.2Ω, L = 250μH
t _R	Rise time	-	17	-		
t _{D(off)}	Turn-off delay	-	7	-		
t _F	Fall time	-	15	-		



Electrical Parameters

T_J=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Reverse Device Characteristics						
V _{SD}	Source-Drain reverse voltage	-	2.2	-	V	V _{GS} =0V, I _{SD} =5A
t _{RR}	Reverse recovery time	-	14	-	ns	I _F =5A, V _{DD} =400V, dI _F /dt=165A/μs
Q _{RR}	Reverse recovery charge	-	6.5	-	nC	



Typical Characteristics

$T_J=25^\circ\text{C}$ unless otherwise stated

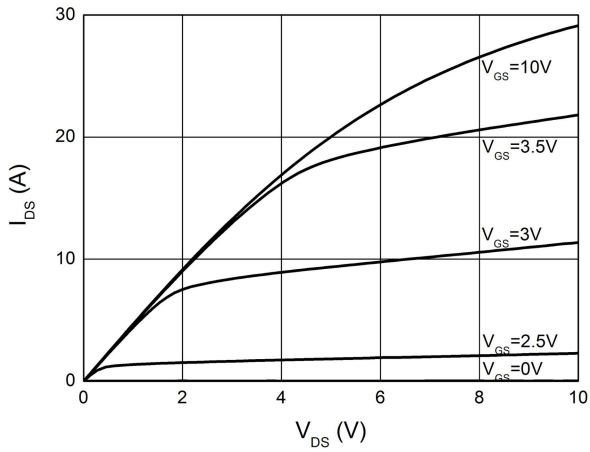


Figure 1. Typical Output Characteristics $T_J=25^\circ\text{C}$

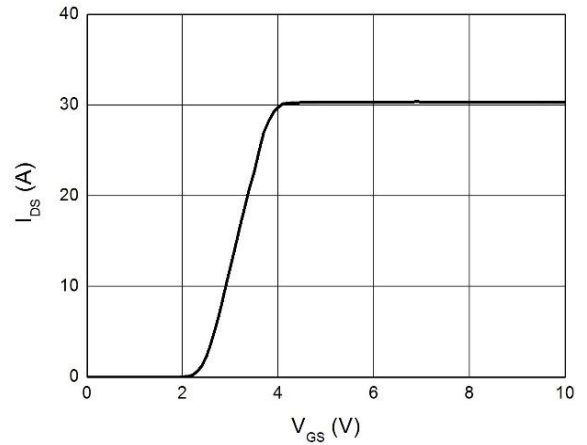


Figure 2. Typical Transfer Characteristics $T_J=25^\circ\text{C}$
($V_{DS}=10\text{V}$)

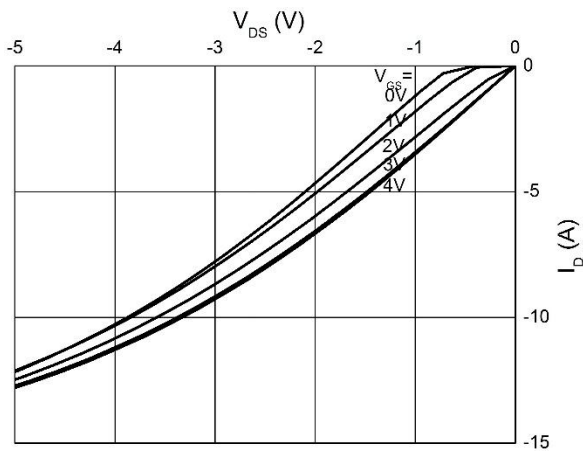


Figure 3. Channel Reverse Characteristics $T_J=25^\circ\text{C}$

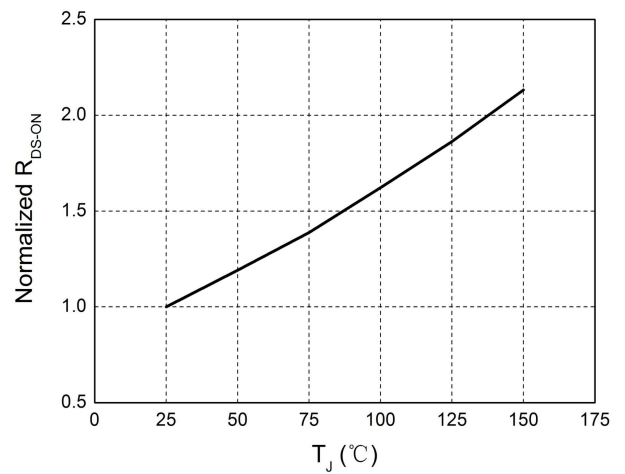


Figure 4. Normalized On-resistance



Typical Characteristics

T_J=25°C unless otherwise stated

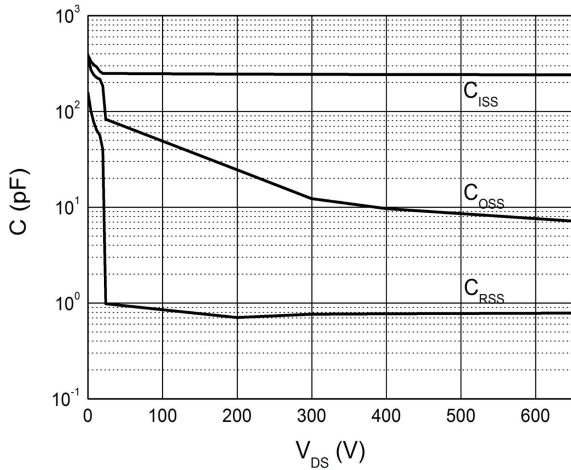


Figure 5. Typical Capacitance (f=1MHz)

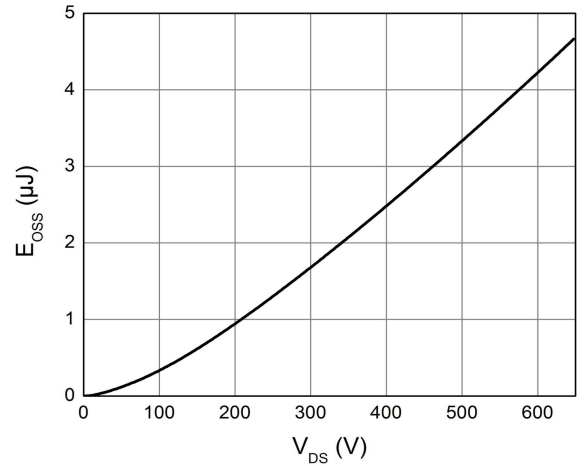


Figure 6. Typical C_{OSS} Stored Energy

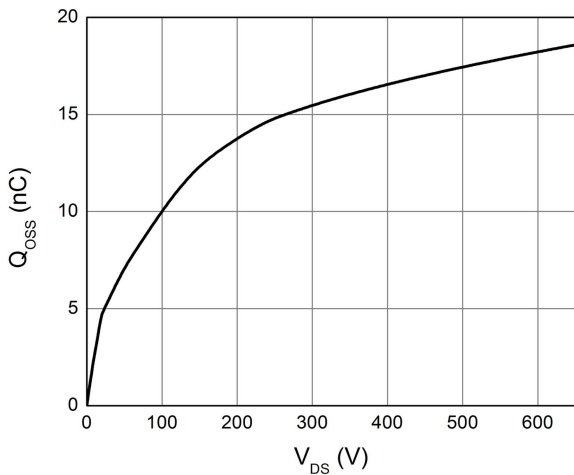


Figure 7. Typical Q_{OSS}

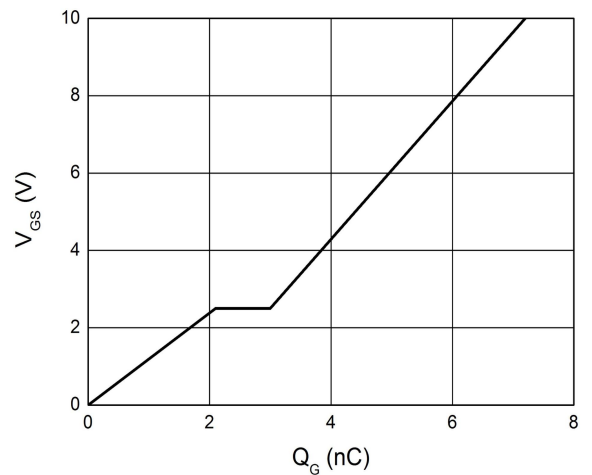


Figure 8. Typical Gate Charge (V_{DS}=400V, I_D=1A)



Typical Characteristics

T_J=25°C unless otherwise stated

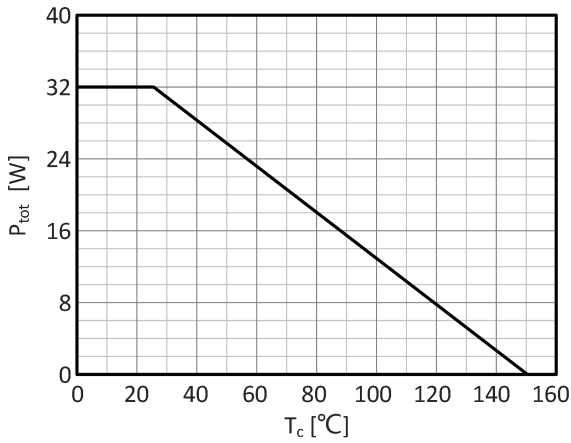


Figure 9. Power Dissipation

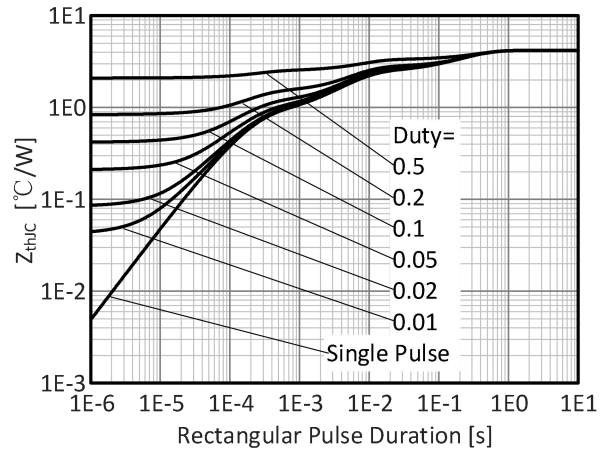


Figure 10. Transient Thermal Resistance

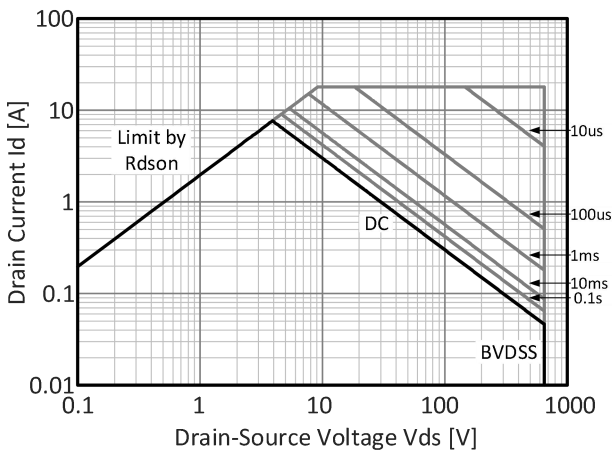


Figure 11. Safe Operating Area T_c=25°C

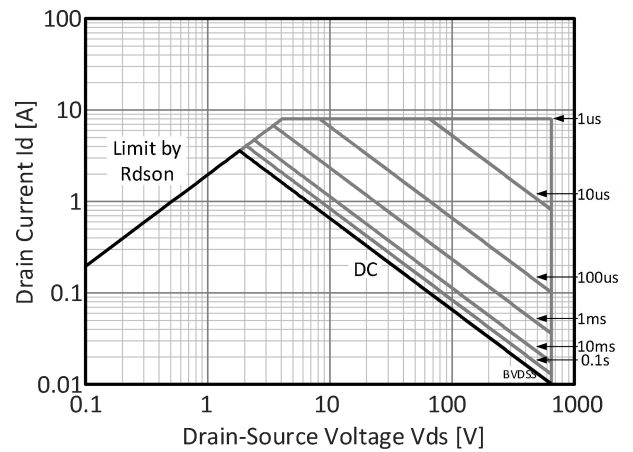


Figure 12. Safe Operating Area T_c=125°C

Typical Characteristics

$T_J=25^\circ\text{C}$ unless otherwise stated

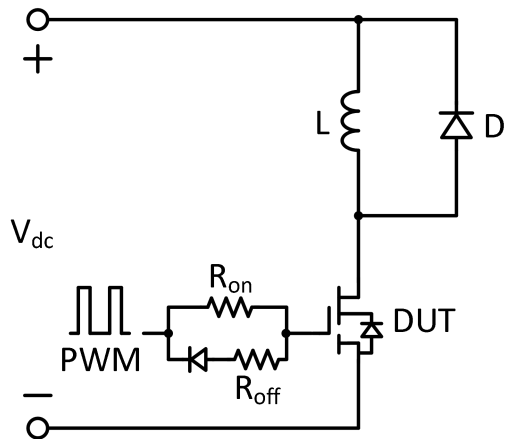


Figure 13. Switching times with inductive load

$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$ to 10V , $I_D=2.1\text{A}$,
 $R_{G-on(ext)}=6.8\Omega$, $R_{G-off(ext)}=2.2\Omega$, $L=250\mu\text{H}$

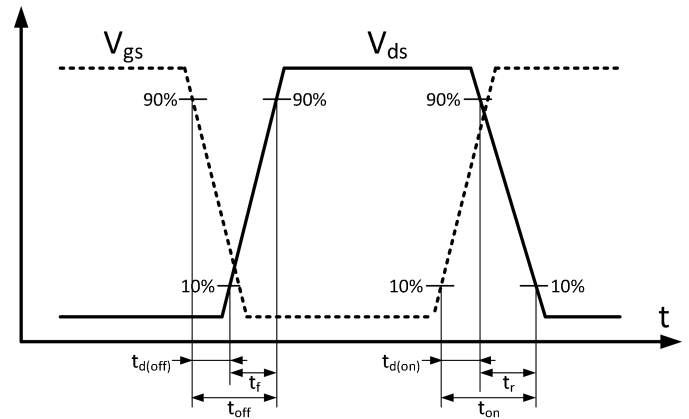
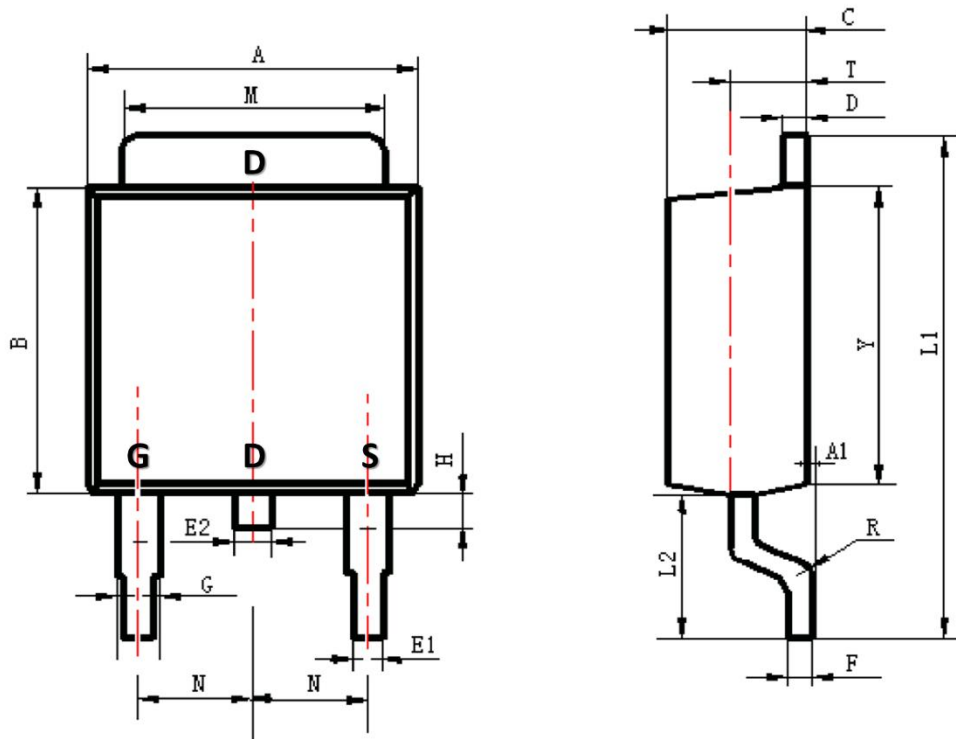


Figure 14. Switching times with waveform

PACKAGE DIMENSIONS

TO252-2L



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
A1	0	0.16
B	5.70	6.30
C	2.10	2.50
D	0.30	0.70
E1	0.60	0.90
E2	0.70	1.00
F	0.30	0.60
G	0.70	1.20
L1	9.60	10.50
L2	2.70	3.10
H	0.40	1.00
M	5.10	5.50
N	2.09	2.49
R	0.3	
T	1.40	1.60
Y	5.10	6.30